Supporting information for

Understanding the contribution of hydroxyl to energy band of semiconductor: $Bi_2O(OH)_2SO_4$ *vs*. $Bi_6S_2O_{15}$

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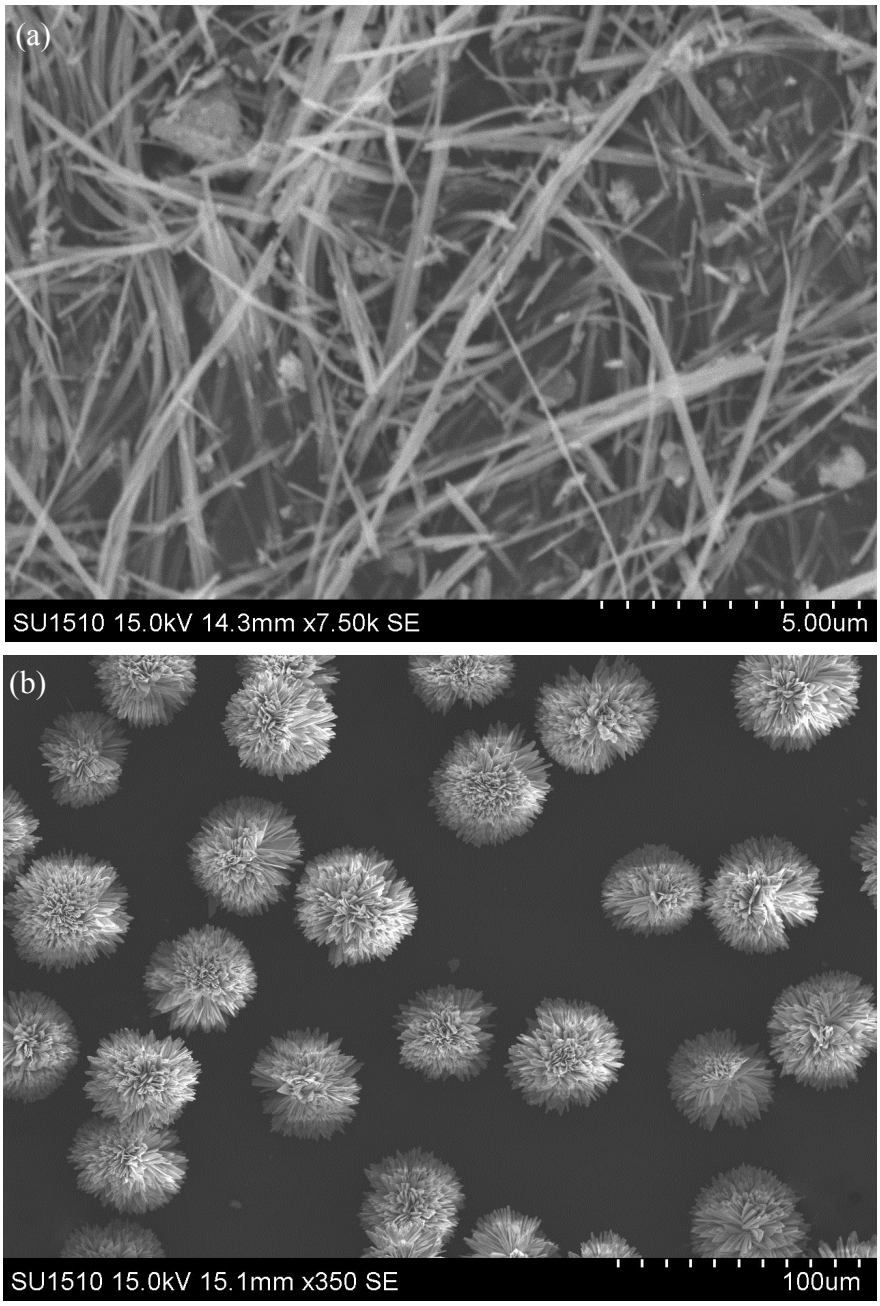

Figure S1. SEM images of as-prepared samples of (a) $Bi_6S_2O_{15}$ and (b) $Bi_2O(OH)_2SO_4$.

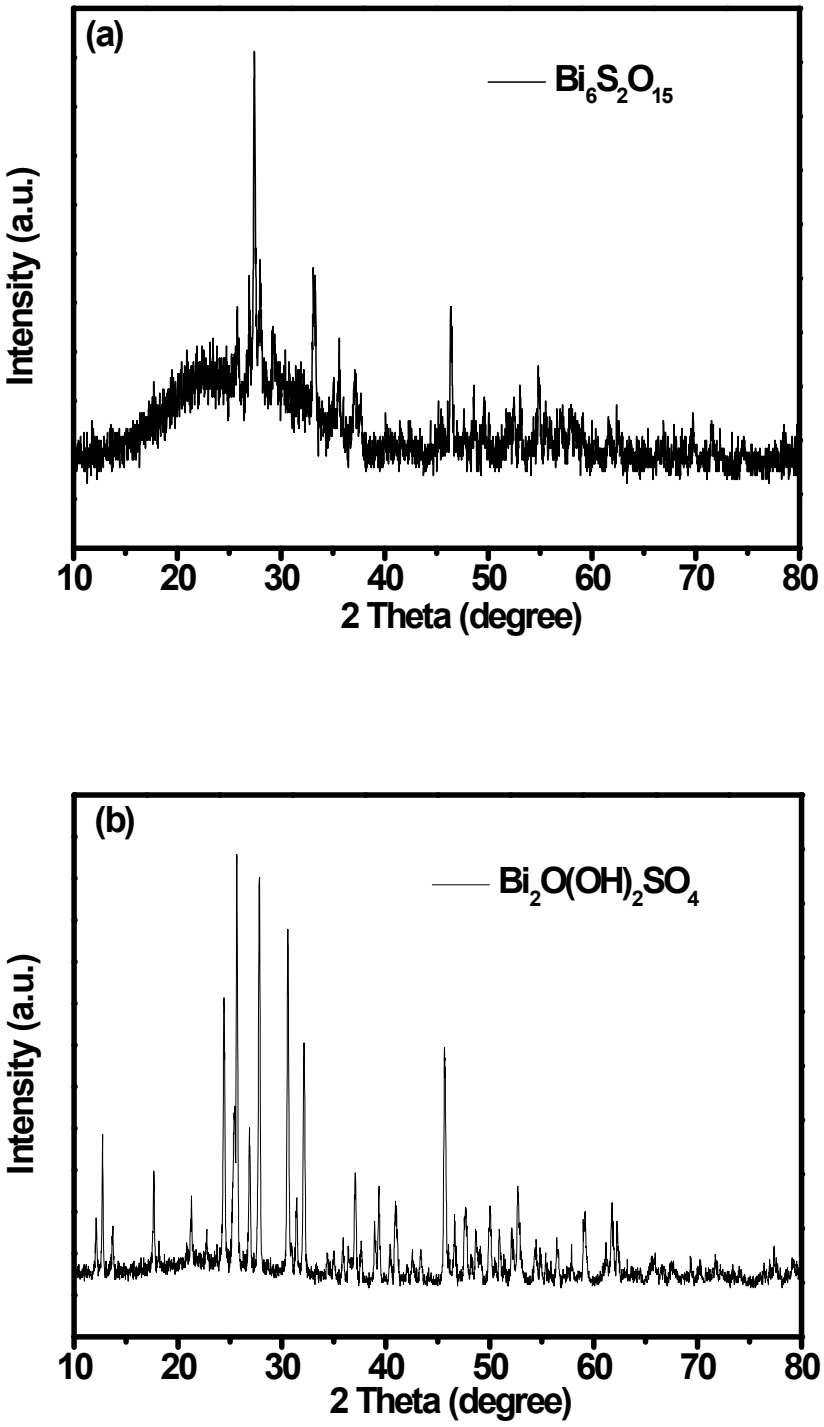

Figure S2. XRD pattern of as-prepared samples of (a) $Bi_6S_2O_{15}$ and (b) $Bi_2O(OH)_2SO_4$.